Novel Wafer-Level Characterization Techniques

- Si Photonics
- Combined RF and optical test for Photonic BiCMOS
- Electromechanical RF-MEMS Characterization based on Laser-Doppler Vibrometry
- Active Load Pull Measurements up to 18 GHz

IHP’s on-Wafer Measurement Service

Get support for your challenging DC and RF measurement tasks

IHP GmbH
Innovations for High Performance Microelectronics
Leibniz-Institut für innovative Mikroelektronik

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Features of IHP’s VLSI Test Equipment

- V93000 SoC High-performance cycle-based production tester
- Tester-per-pin architecture
- Device power supplies:
  - 12 channels: ±8V, max. 16A
  - 32 channels: 0-7V, max. 48A @3V
- Up to 320 digital channels
  - 256 channels with up to 1.6Gb/s
  - 64 channels with up to 8Gb/s
- Analog resources
  - 4 waveform generators, max 200MHz @50Ms/s
  - 4 digitizers, max 16 bit @300MHz
- Fully automatic wafer prober
- Wafer size: 125 mm, 150 mm, 200 mm
- Temperature range: -40°C to +150°C
- Loader for cassettes with up to 25 wafers

Measurement Capabilities

- DC down to 1fA current resolution
- True Kelvin measurements (force/sense)
- 48 channel low leakage switch matrix
- C(V) from 20Hz to 1MHz
- TLP ESD characterization up to 7kV HBM equivalent
- Impedance up to 3GHz
- S-Parameters up to 170GHz (500GHz on request)
- 4Port S-Parameters up to 50GHz
- X-Parameters up to 50GHz
- Spectrum analysis
- Low frequency noise
- High frequency noise from 2GHz to 26GHz
- Wafer size: all sizes ≤ 300mm
- Semi-automatic mapping
- Temperature range: -60°C to +300°C (for S-Parameters the temperature range is limited)

Standard pad configuration

- Standard pad configuration for S-Parameters: 100µm GSG

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Device Measurements

Functional Test Equipment

Circuit Measurements